

ROHSV EARTH FRIEND

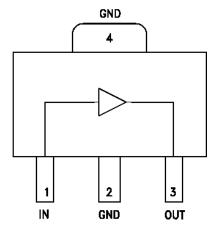
#### v02.0813

#### **Typical Applications**

The HMC740ST89E is ideal for:

- Cellular/3G & WiMAX/4G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment
- IF & RF Applications

#### **Functional Diagram**



## HMC740ST89E

## InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

#### Features

P1dB Output Power: +18 dBm Gain: 15 dB Output IP3: +40 dBm Cascadable 50 Ohm I/Os Single Supply: +5V Industry Standard SOT89 Package Robust 1000V ESD, Class 1C Stable Current Over Temperature Active Bias Network

#### **General Description**

The HMC740ST89E is an InGaP Heterojunction Bipolar Transistor (HBT) Gain Block MMIC SMT amplifier covering 0.05 to 3 GHz. Packaged in an industry standard SOT89, the amplifier can be used as a cascadable 50 Ohm RF or IF gain stage as well as a PA or LO driver with up to +18 dBm output power. The HMC740ST89E offers 15 dB of gain with a +40 dBm output IP3 at 100 MHz, and can operate directly from a +5V supply. The HMC740ST89E exhibits excellent gain and output power stability over temperature, while requiring a minimal number of external bias components.

#### Electrical Specifications, Vcc = 5V, $T_{A}$ = +25° C Parameter Min Тур. Max. Min. Max. Units Typ **Frequency Range** 0.05 - 1 0.05 - 3 GHz Gain 12 15 11 15 dB Gain Flatness ±0.1 ±0.7 dB Gain Variation over Temperature 0.006 0.003 0 006 dB/ °C 0.003 Input Return Loss 15 dB 18 Output Return Loss 18 18 dB **Reverse Isolation** 20 21 dB Output Power for 1 dB Compression (P1dB) 17 15.5 18 14.5 dBm Output Third Order Intercept (IP3) 38 32 dBm (Pout= 0 dBm per tone, 1 MHz spacing) Noise Figure 3.5 3.5 dB Supply Current (Icq) 88 88 mA

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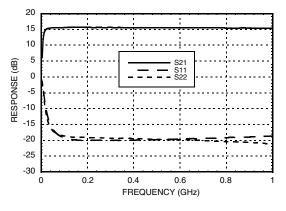


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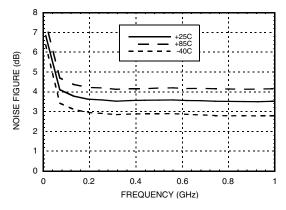
# ROHS V

**IF Band Performance** 

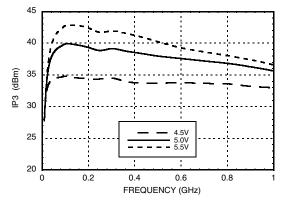
#### Gain & Return Loss



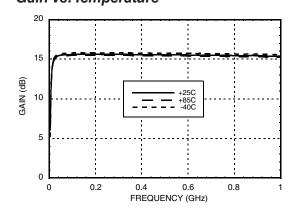
Noise Figure vs. Temperature



#### Output IP3 vs. Vcc



## Gain vs. Temperature

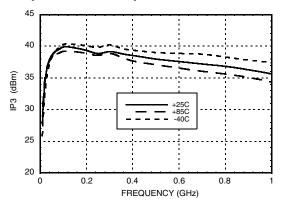


**HMC740ST89E** 

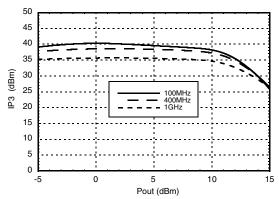
InGaP HBT ACTIVE BIAS

MMIC AMPLIFIER, 0.05 – 3 GHz

#### Output IP3 vs. Temperature



#### Output IP3 vs. Output Power



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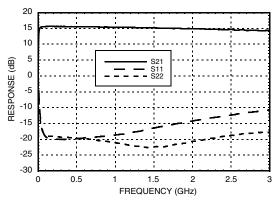
## HMC740ST89E

#### InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

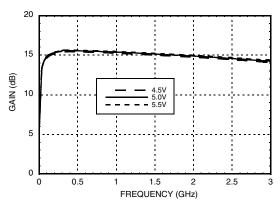


#### **Broadband Performance**

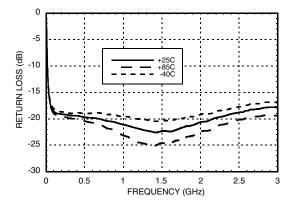
#### Gain & Return Loss



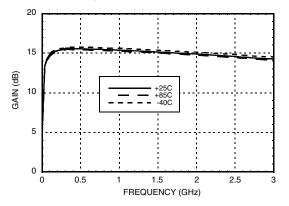
Gain vs. Vcc



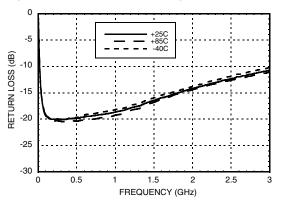
**Output Return Loss vs. Temperature** 



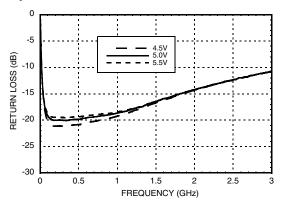
Gain vs. Temperature



Input Return Loss vs. Temperature



Input Return Loss vs. Vcc



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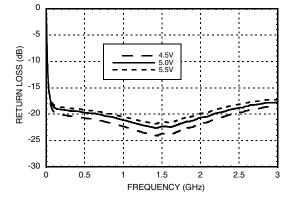


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### InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

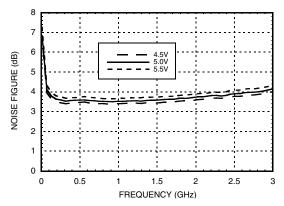


#### **Output Return Loss vs. Vcc**

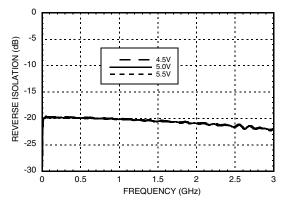


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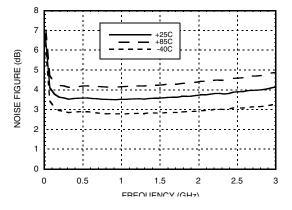
#### Noise Figure vs. Vcc



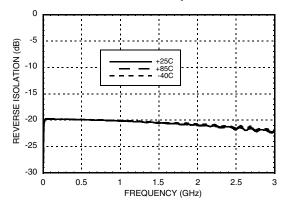
#### **Reverse Isolation vs. Vcc**



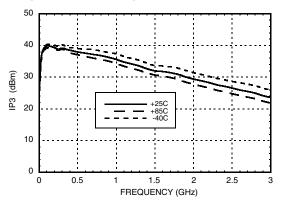
#### Noise Figure vs. Temperature



#### Reverse Isolation vs. Temperature



#### Output IP3 vs. Temperature



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## **HMC740ST89E**

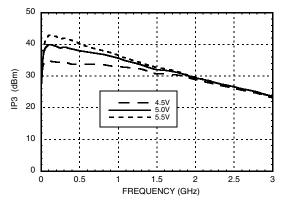
InGaP HBT ACTIVE BIAS

MMIC AMPLIFIER, 0.05 - 3 GHz

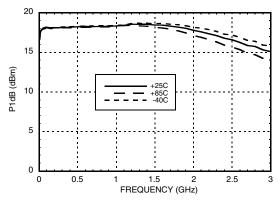
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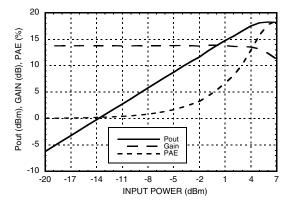
#### Output IP3 vs. Vcc



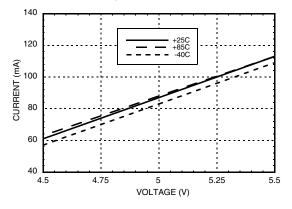
#### P1dB vs. Temperature



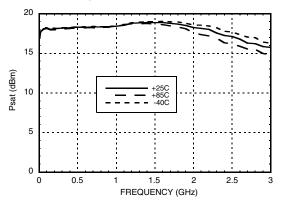
#### Power Compression @ 500 MHz



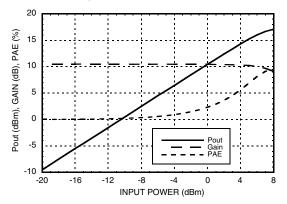
#### Current vs. Temperature



#### Psat vs. Temperature



#### Power Compression @ 2 GHz



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#### Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+5.5 Vdc		
RF Input Power (RFIN)	N) +15 dBm		
Junction Temperature	150 °C		
Continuous Pdiss (T = 85 °C) (derate 10.23 mW/°C above 85 °C)	0.66 W		
Thermal Resistance (junction to lead)	97.78 °C/W		
Storage Temperature	-65 to +150 °C		
Operating Temperature	-40 to +85 °C		
ESD Sensitivity (HMB)	Class 1C		



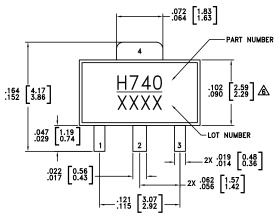
ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

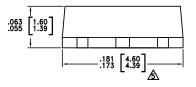
MMIC AMPLIFIER, 0.05 - 3 GHz

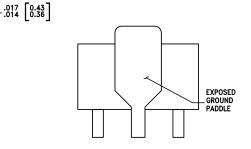
**HMC740ST89E** 

InGaP HBT ACTIVE BIAS

#### **Outline Drawing**







NOTES:

1 PACKAGE B

1. PACKAGE BODY MATERIAL: MOLDING COMPOUND MP-180S OR EQUIVALENT.

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2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.

3. LEAD PLATING: 100% MATTE TIN.
4. DIMENSIONS ARE IN INCHES [MILLIMETERS]

A. DIMENSIONS ARE IN INCRES [IMILLIMETERS]

<u>A</u>DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.1511111 FER SIDE.

7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

#### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[1]</sup>
HMC740ST89E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>H740</u> XXXX

[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 260 °C

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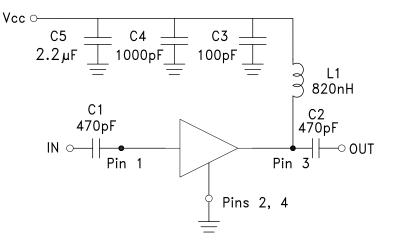


## InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

#### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic	
1	IN	This pin is DC coupled. An off chip DC blocking capacitor is required.		
3	OUT	RF output and DC Bias (Vcc) for the output stage.		
2, 4	GND	These pins and package bottom must be connected to RF/DC ground.		

#### **Application Circuit**



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